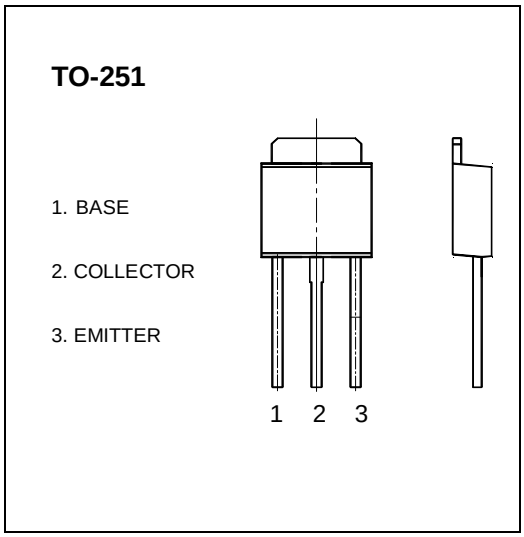
Transys Electronics LIMITED

TO-251 Plastic-Encapsulated Transistors

3DA752 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 1.2 W (Tamb=25℃)

Collector current

$I_{CM:}$ 2 A

Collector-base voltage

$V_{(BR)CBO}$: 40 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=10mA, I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=2V, I_C=500mA	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)1}$	I_C=2A, I_B=0.2A			0.8	V
	$V_{CE(sat)2}$	I_C=1.5A, I_B=30mA			2	V
Transition frequency	f_T	V_{CE}=5V, I_C=500mA		120		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Range	100-200	160-320	200-400
Marking			